

FIG.1(a) prior art

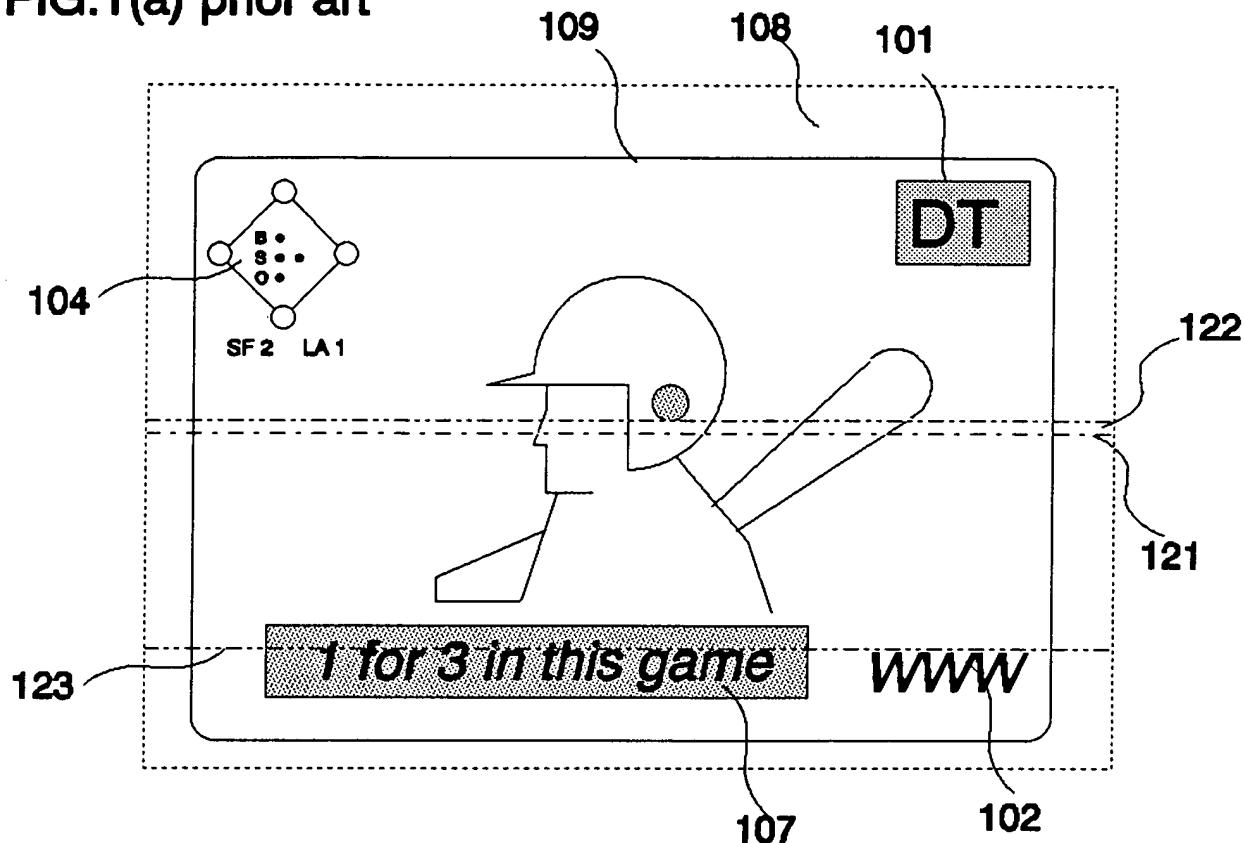


FIG.1(b) prior art

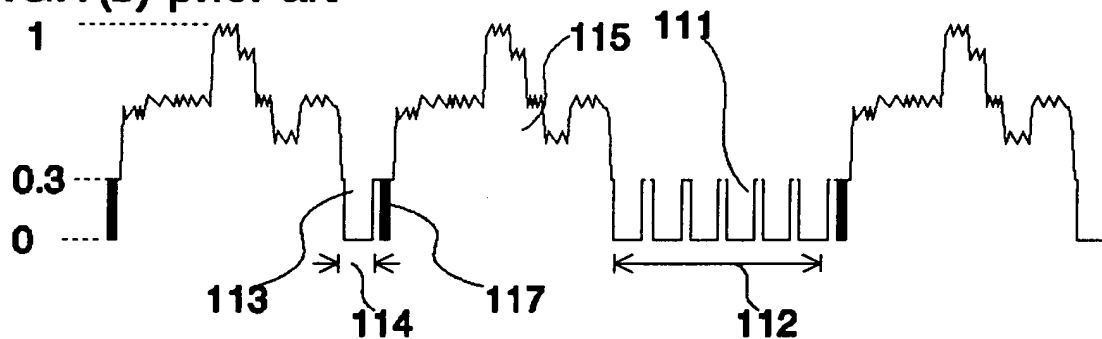


FIG.1(c) prior art

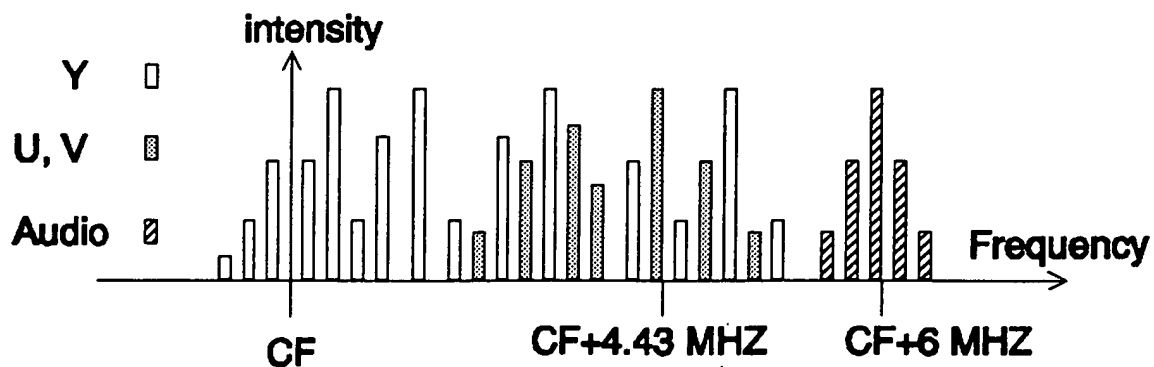


FIG.1(d) prior art

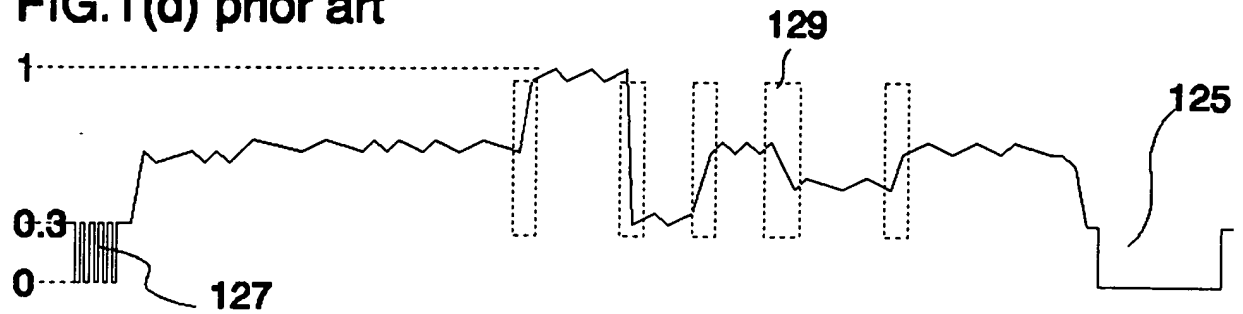


FIG.1(e) prior art

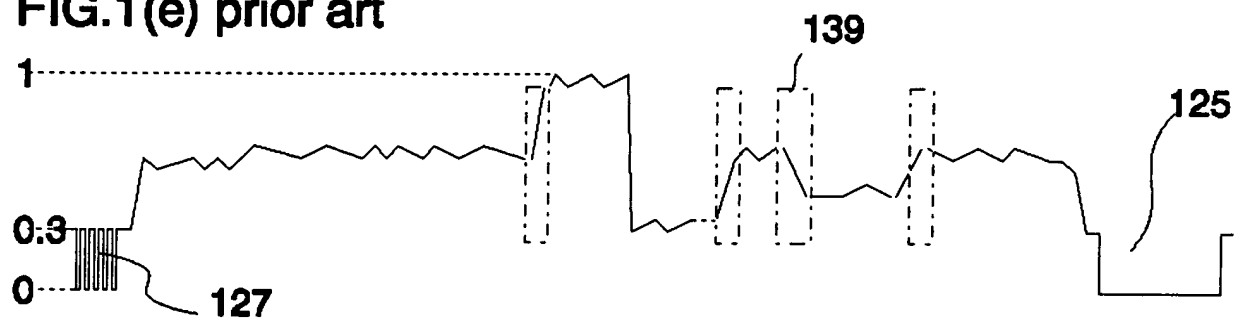


FIG.1(f) prior art

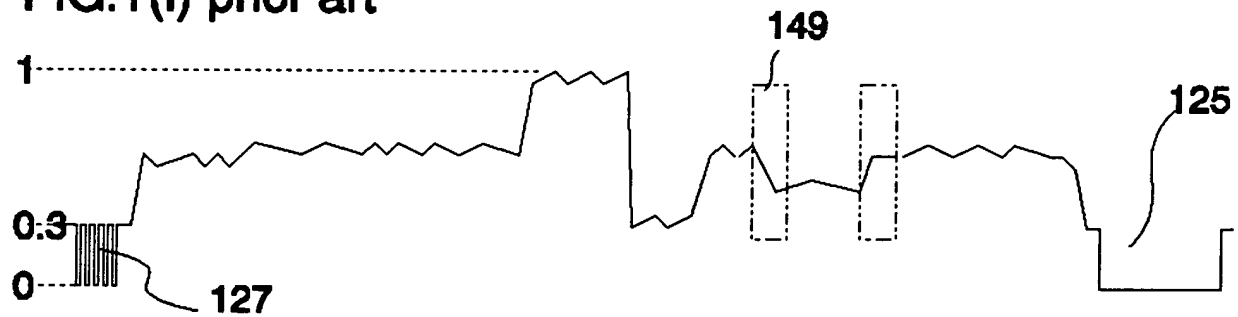


FIG.1(g) prior art

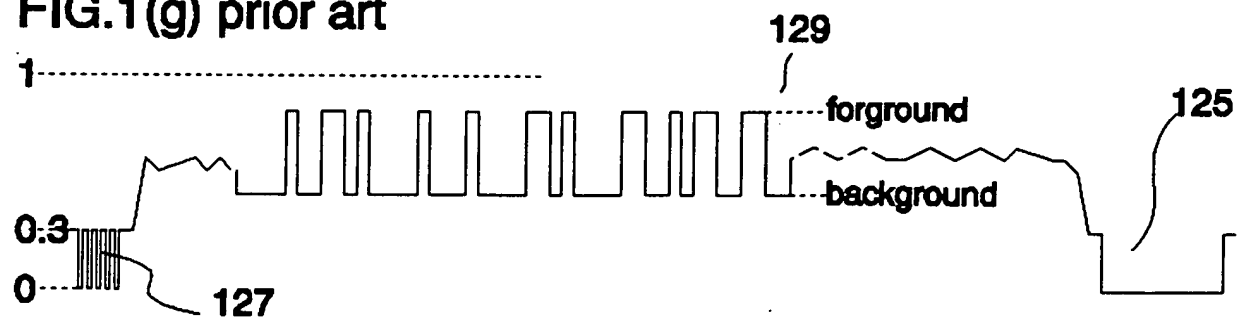


FIG.2(a)

A cross-sectional view of a semiconductor device structure. The structure consists of a substrate 125 with a series of vertical lines on its left side. A layer 0.3 is deposited on top of the substrate. A layer 201 is formed on top of layer 0.3, with a dashed line indicating its boundary. A layer 1 is formed on top of layer 201, with a dashed line indicating its boundary. A layer 201 is formed on top of layer 1, with a dashed line indicating its boundary. A layer 125 is formed on top of layer 201, with a dashed line indicating its boundary.

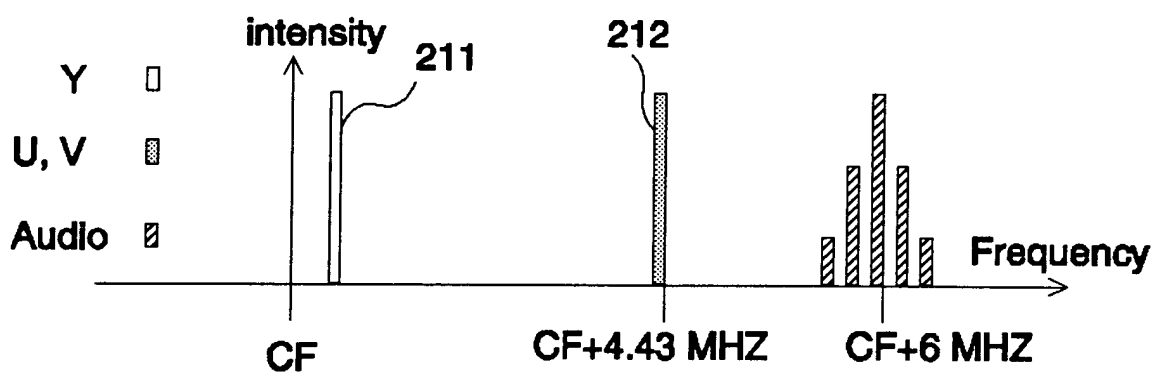


Figure 1 is a bar chart titled 'intensity' on the y-axis and 'Frequency' on the x-axis. The x-axis labels are CF, F0, F1, F2, F3, CF+4.43 MHz, F4, F5, CF+6 MHz, and a final unlabeled peak. The legend indicates three signal types: Y (white bars), U, V (dotted bars), and Audio (hatched bars). The Audio signal shows a prominent peak at CF+6 MHz, while the Y and U, V signals show much lower intensities across the frequency range.

FIG.2(e)

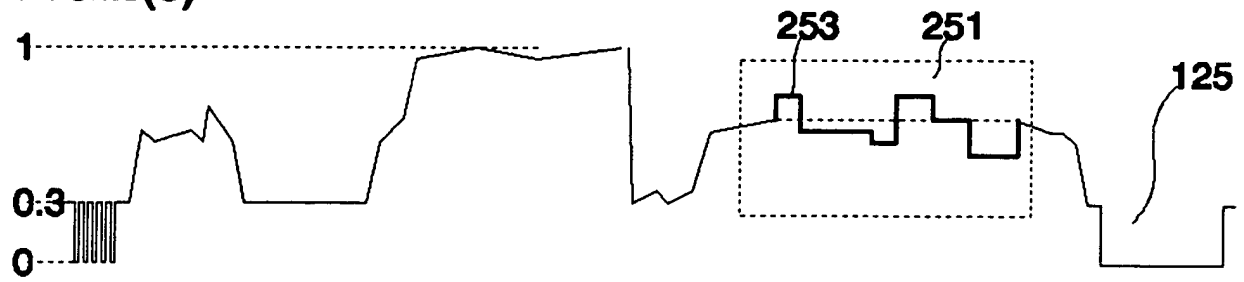


FIG.2(f)

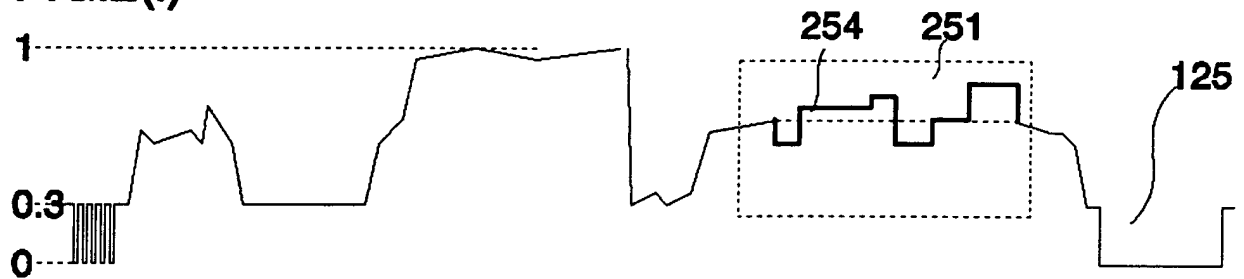


FIG.2(g)

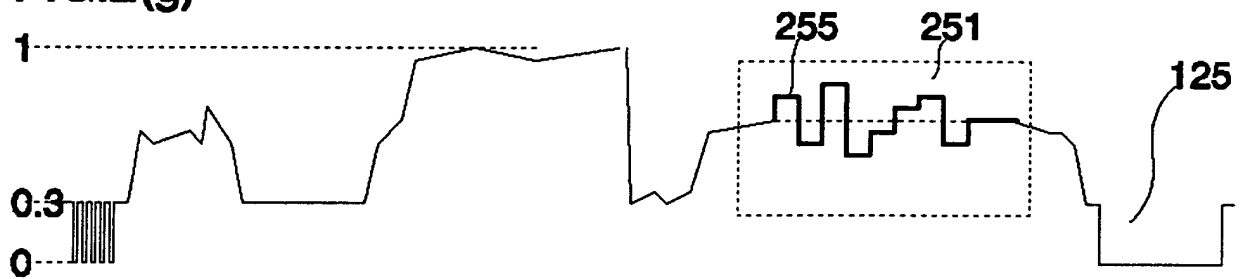


FIG.2(h)

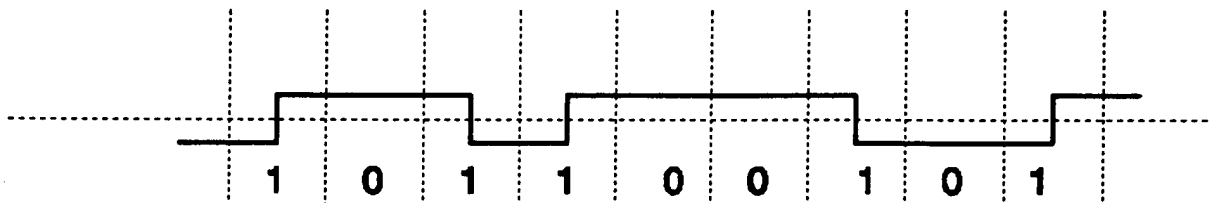


FIG.3(a)

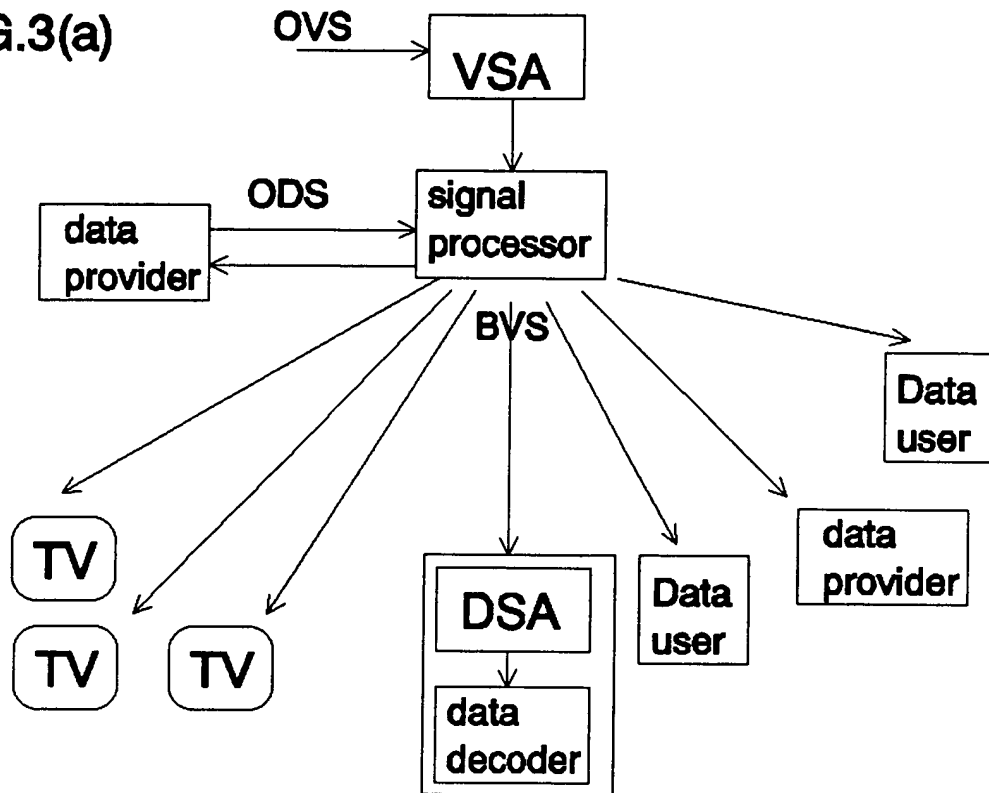


FIG.3(b)

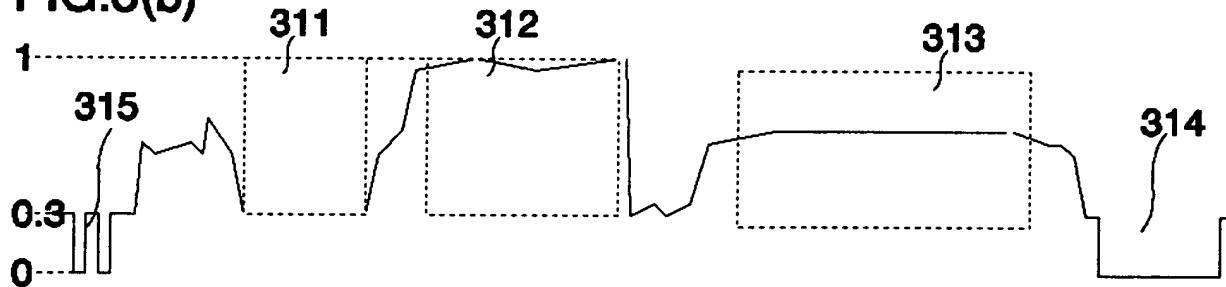


FIG.3(c)

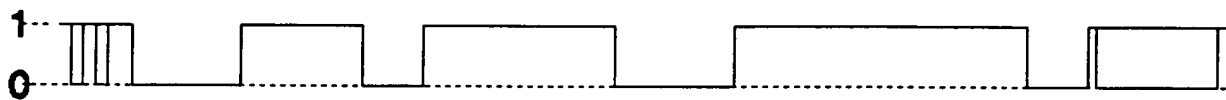


FIG.3(d)

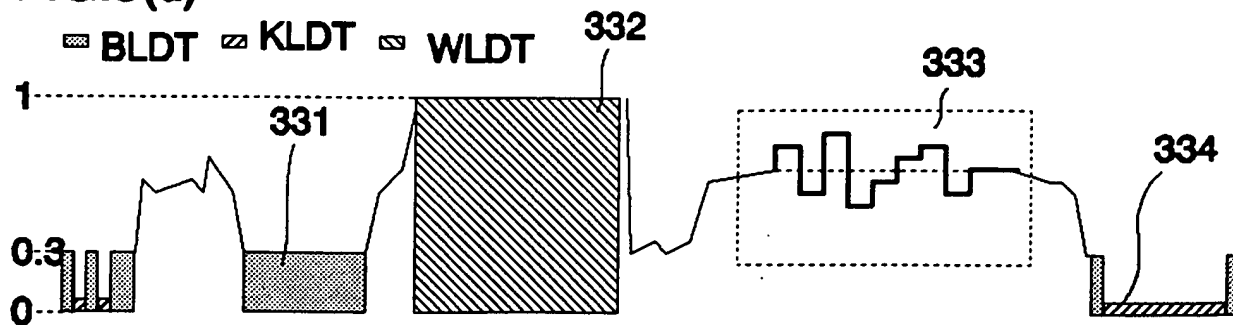


FIG.4(a)



FIG.4(b)



FIG.4(c)



FIG.5(a)

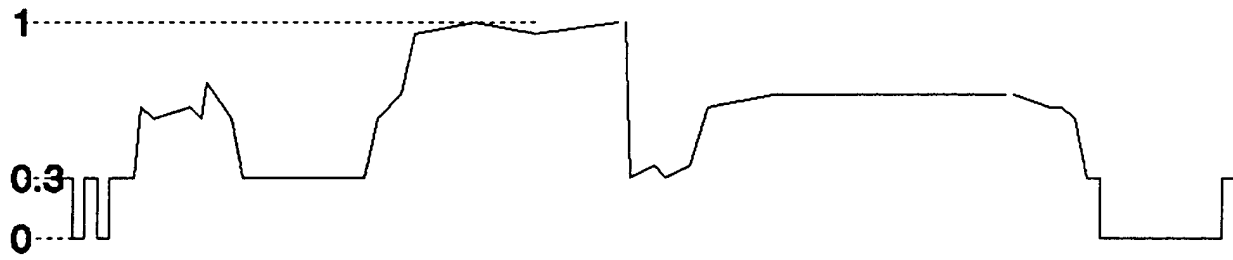


FIG.5(b)



FIG.5(c)

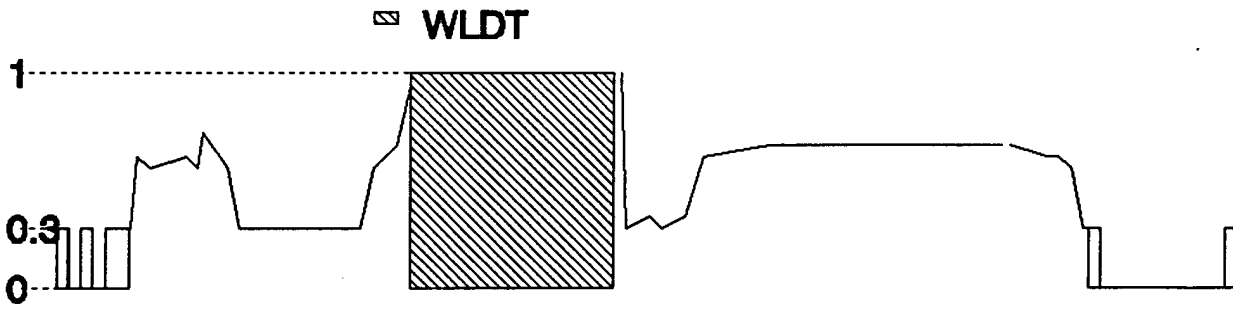


FIG.6(a)

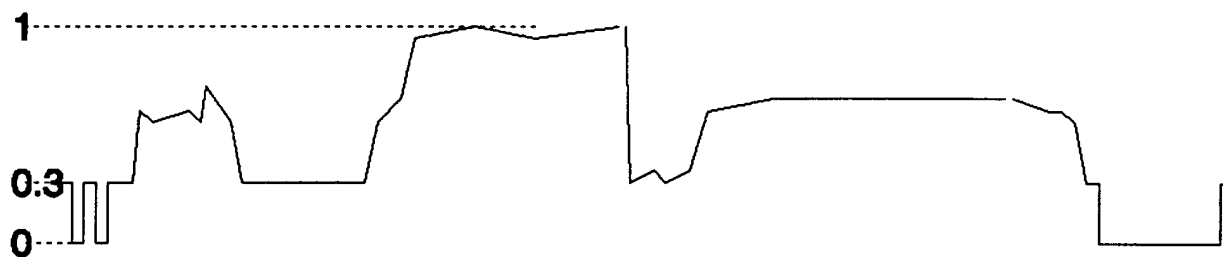


FIG.6(b)

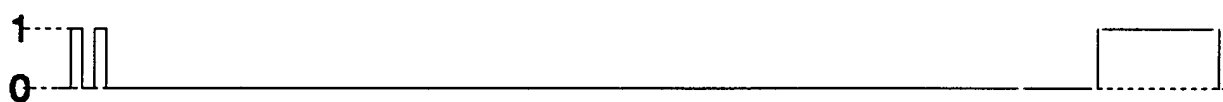


FIG.6(c)

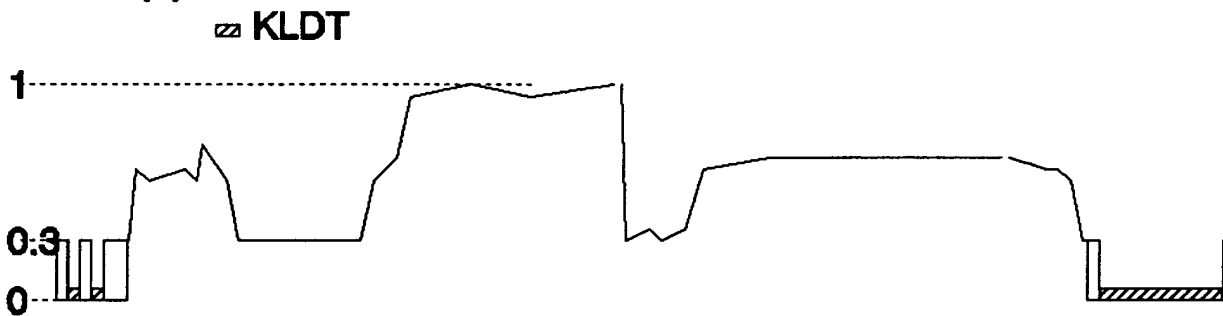
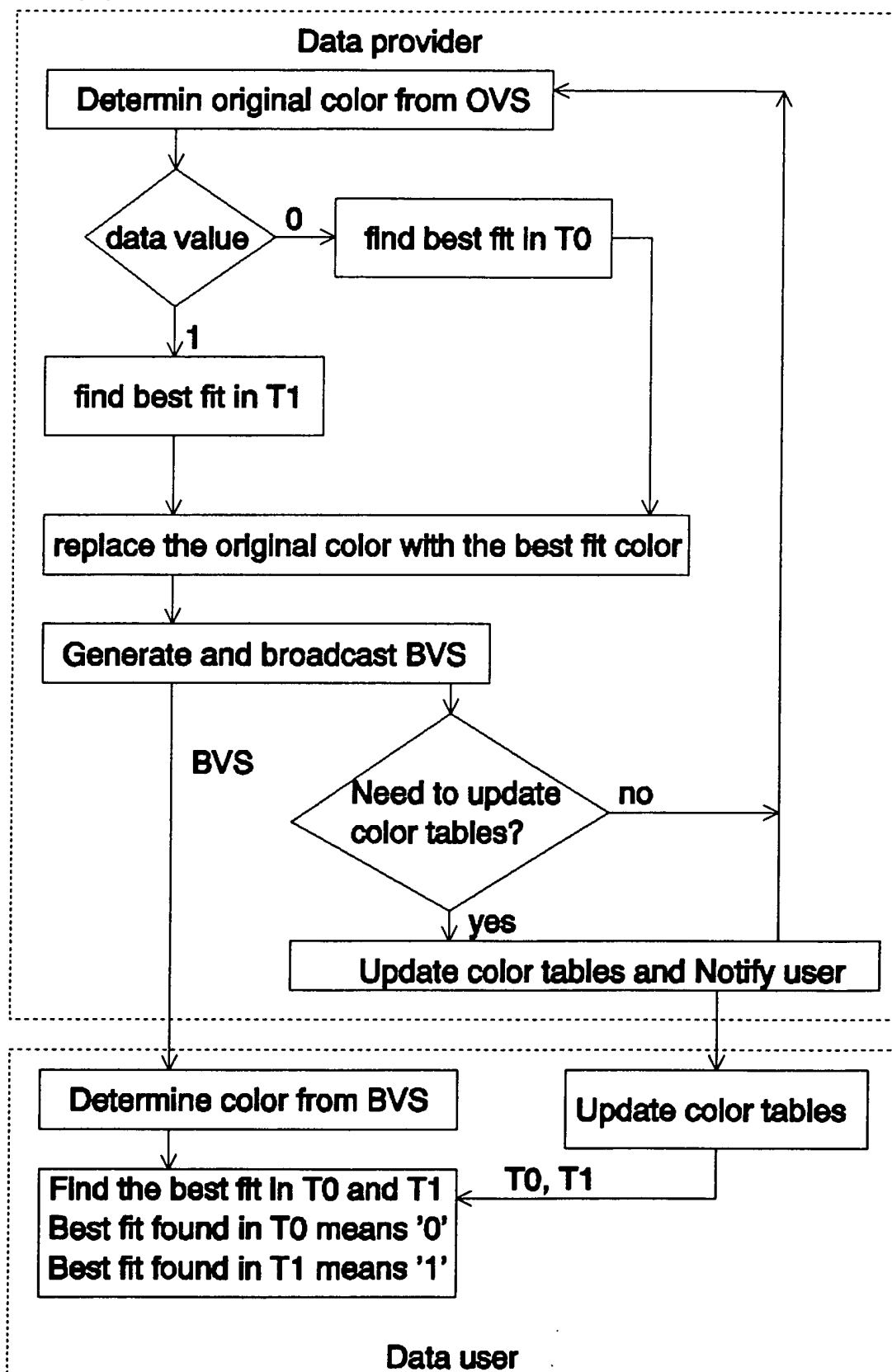


FIG. 7(a)



00000" 60E6560

SECRET

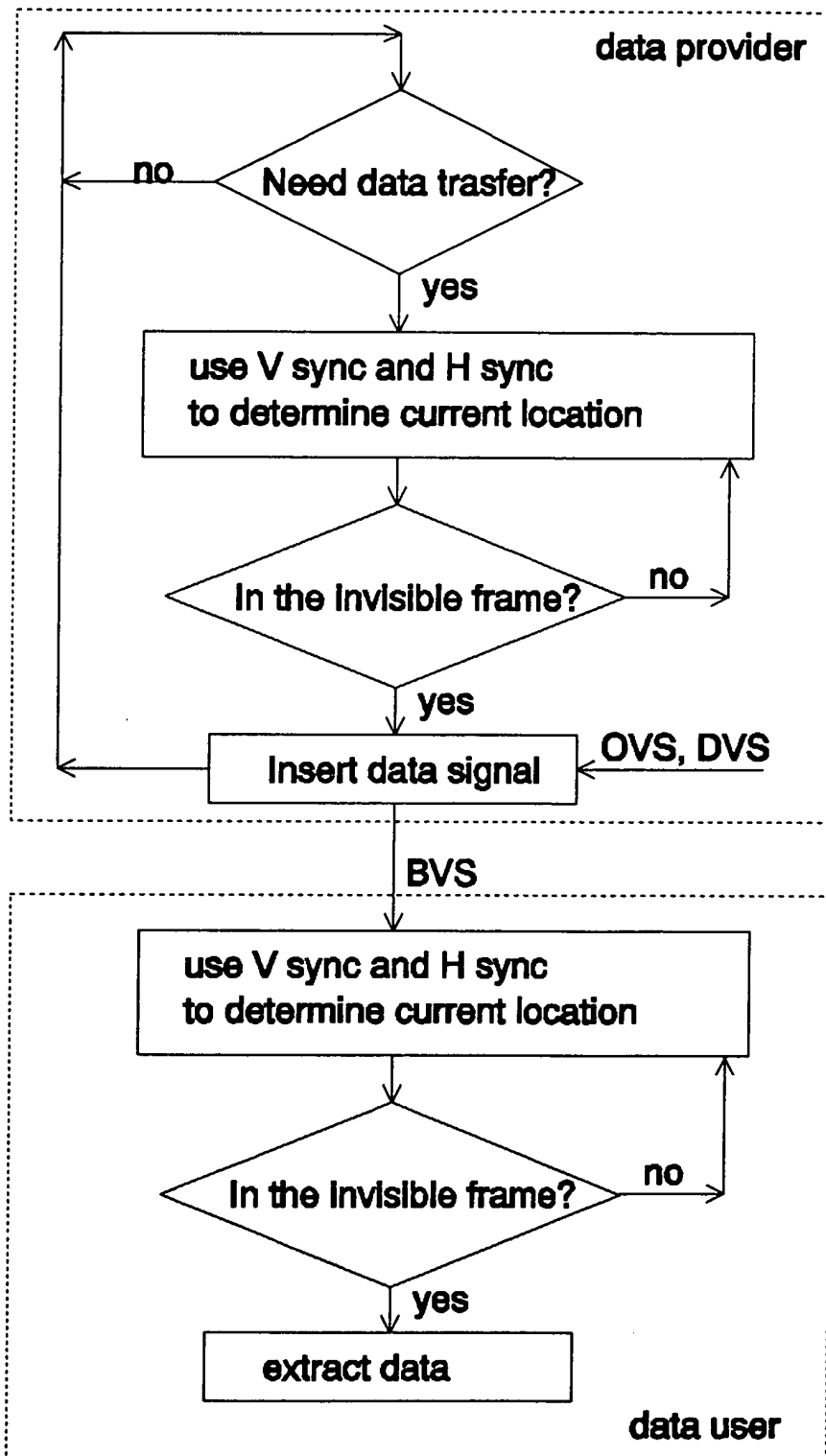


FIG. 8(a)

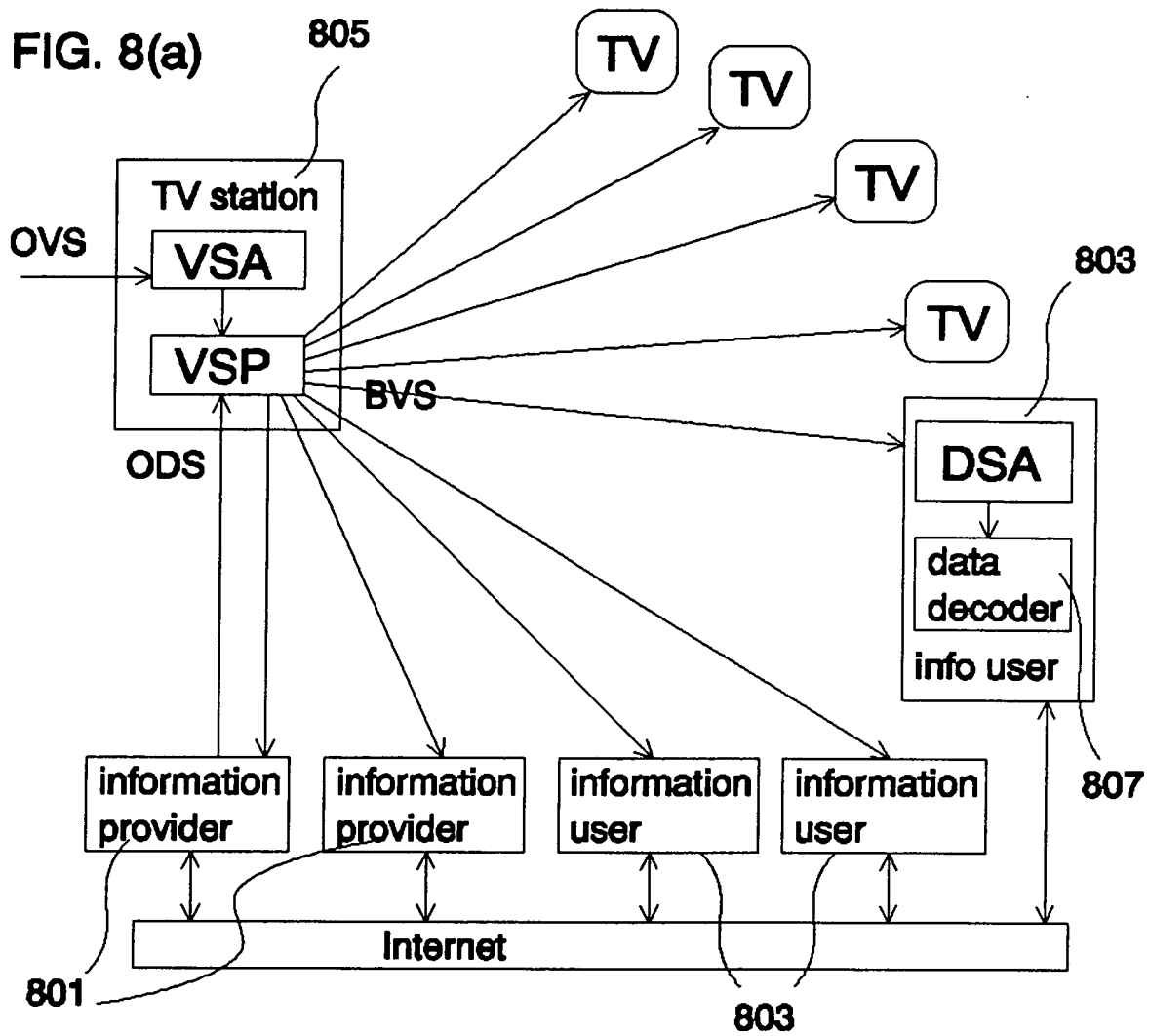
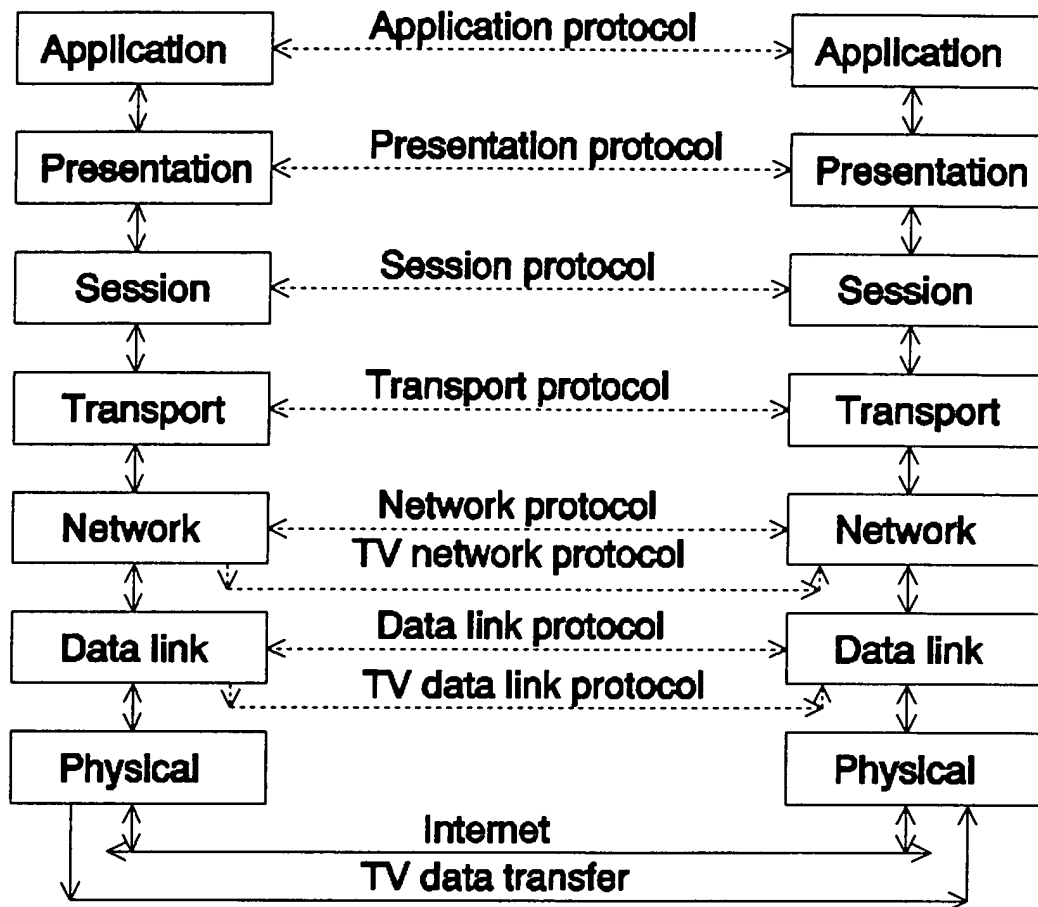


FIG. 8(b)



00000"60E6E560

FIG. 9(a)

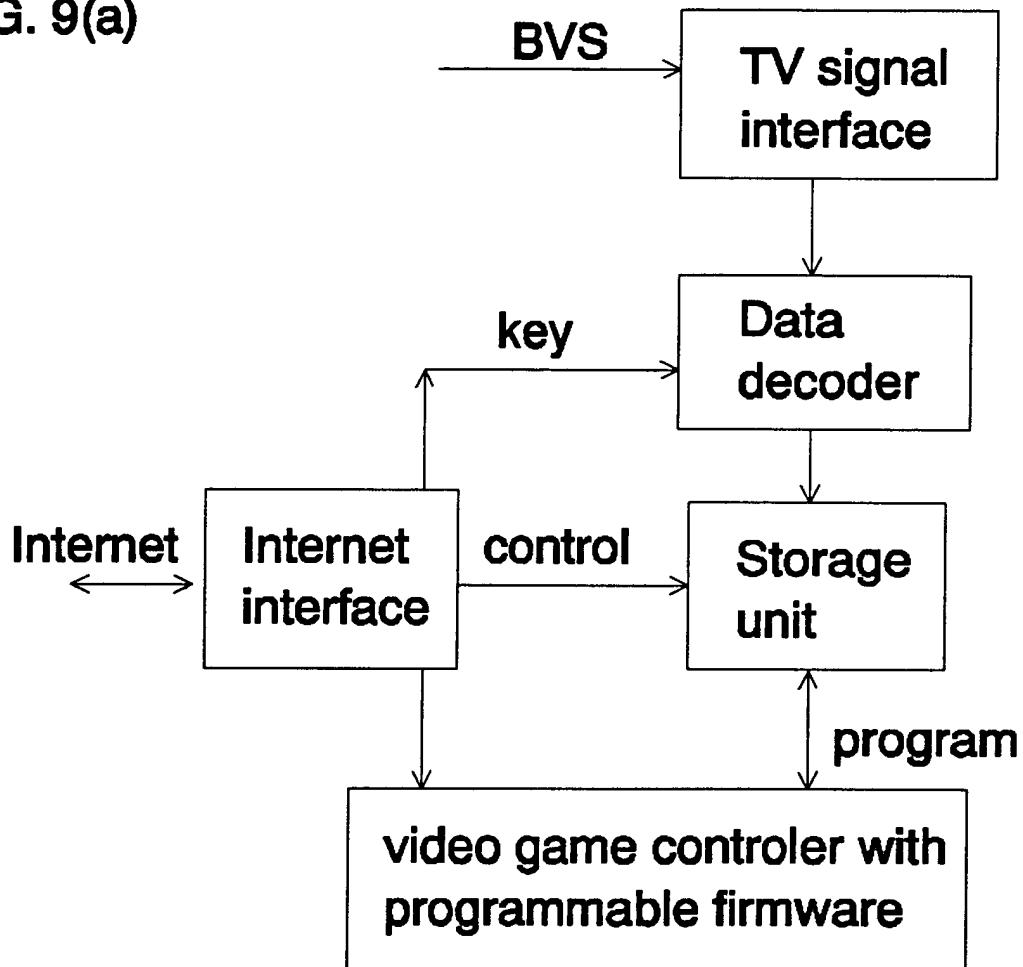
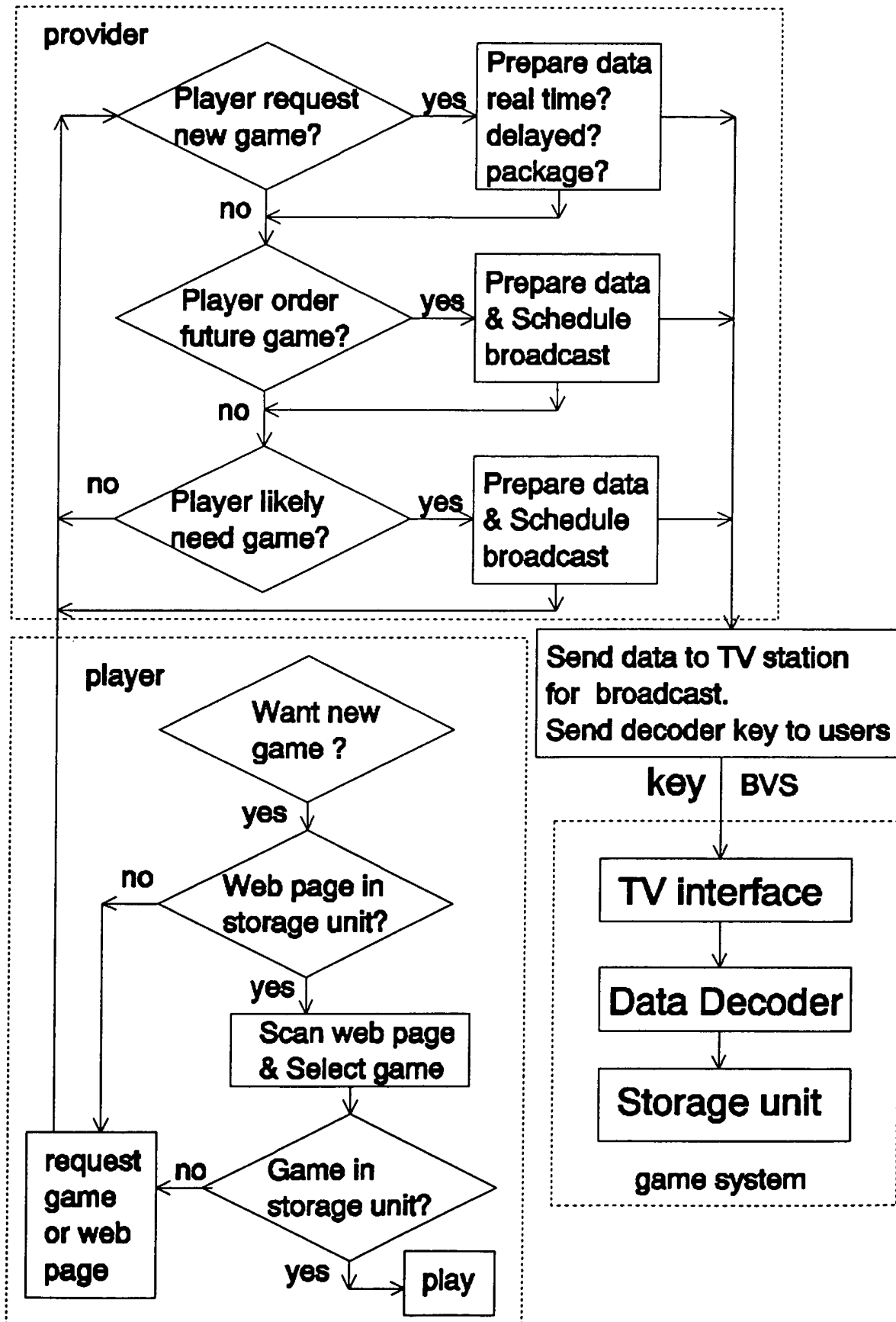


FIG. 9(b)



00000" 00000000

FIG. 10

